

# **N-Channel Power MOSFET**

600V, 0.6A, 5Ω

#### **FEATURES**

- Robust high voltage termination
- Avalanche energy specified
- Diode is characterized for use in bridge circuits
- Source to Drain diode recovery time comparable to a discrete fast recovery diode.

KEY PERFORMANCE PARAMETERS				
PARAMETER	PARAMETER VALUE UNIT			
V <sub>DS</sub>	600	V		
R <sub>DS(on)</sub> (max)	5	Ω		
$Q_g$	13	nC		

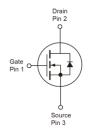
#### **APPLICATION**

- Power Supply
- Lighting
- Charger





**SOT-223** 



Notes: MSL 3 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		$V_{DS}$	600	٧
Gate-Source Voltage		$V_{GS}$	±30	V
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$		0.6	^
	T <sub>C</sub> = 100°C	l <sub>D</sub>	0.36	А
Pulsed Drain Current (Note 2)		I <sub>DM</sub>	1.5	А
Total Power Dissipation @ T <sub>C</sub> = 25°C		P <sub>DTOT</sub>	2.5	W
Single Pulsed Avalanche Energy (Note 3)		E <sub>AS</sub>	62	mJ
Single Pulsed Avalanche Current (Note 3)		I <sub>AS</sub>	2.5	А
Operating Junction Temperature		$T_J$	150	°C
Operating Junction and Storage Temperature Range		$T_J, T_STG$	- 55 to +150	°C

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	R <sub>eJC</sub>	15	°C/W	
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	55.8	°C/W	

**Notes:**  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\theta JA}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.  $R_{\theta JA}$  shown below for single device operation on FR-4 PCB with minimum recommended footprint in still air



ELECTRICAL SPECIFICATIONS (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	600			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V <sub>GS(TH)</sub>	2		4	V
Gate Body Leakage	$V_{GS} = \pm 30 \text{V}, V_{DS} = 0 \text{V}$	I <sub>GSS</sub>	-		±100	nA
Zero Gate Voltage Drain Current	V <sub>DS</sub> =600V, V <sub>GS</sub> =0V	I <sub>DSS</sub>	ł		1	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 0.6A$	R <sub>DS(ON)</sub>	ł	3.6	5	Ω
Forward Transconductance	$V_{DS} = 10V, I_D = 0.2A$	<b>g</b> fs	1	0.8		S
Dynamic (Note 5)						
Total Gate Charge	\/ 400\/ L 0.04	$Q_g$	ł	13		
Gate-Source Charge	$V_{DS} = 400V, I_{D} = 0.6A,$ $V_{GS} = 10V$	$Q_{gs}$	-	2		nC
Gate-Drain Charge		$Q_{gd}$	-	6		
Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f =1.0MHz	C <sub>iss</sub>	ł	435		
Output Capacitance		C <sub>oss</sub>		56		pF
Reverse Transfer Capacitance	1 = 1.01011 12	C <sub>rss</sub>		9.2		
Switching (Note 6)						
Turn-On Delay Time		t <sub>d(on)</sub>		12		
Turn-On Rise Time	$V_{GS} = 10V, I_D = 0.6A,$ $V_{DD} = 300V, R_G = 18\Omega,$	t <sub>r</sub>	-	21		
Turn-Off Delay Time		$t_{d(off)}$	-	30		ns
Turn-Off Fall Time		t <sub>f</sub>	-	24		
Source-Drain Diode (Note 4)						
Forward On Voltage	$I_S = 0.6A, V_{GS} = 0V$	$V_{SD}$	-	0.85	1.15	V

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## Notes:

- 1. Current limited by package
- 2. Pulse width limited by the maximum junction temperature
- 3. L=20mH,  $I_{AS}=2.5A$ ,  $V_{DD}=50V$ ,  $R_{G}=25\Omega$ , Starting  $T_{J}=25^{\circ}C$
- 4. Pulse test: PW ≤ 300µs, duty cycle ≤ 2%
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.





## **ORDERING INFORMATION**

PART NO.	PACKAGE	PACKING
TSM2N60SCW RPG	SOT-223	2,500pcs / 13" Reel

### Note:

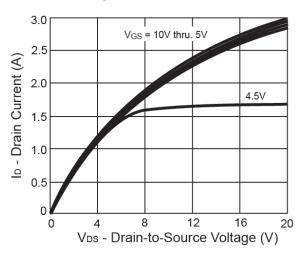
- 1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- 2. Halogen-free according to IEC 61249-2-21 definition



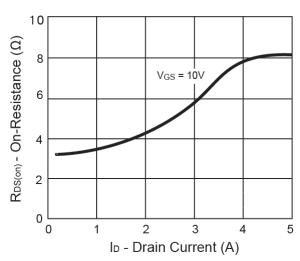
# **CHARACTERISTICS CURVES**

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 

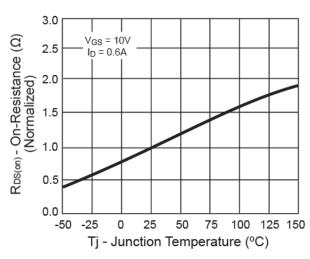
#### **Output Characteristics**



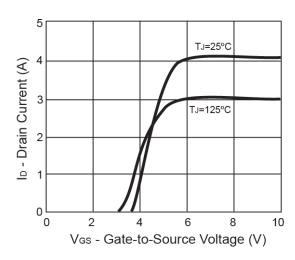
#### **On-Resistance vs. Drain Current**



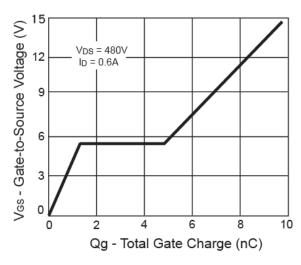
## On-Resistance vs. Junction Temperature



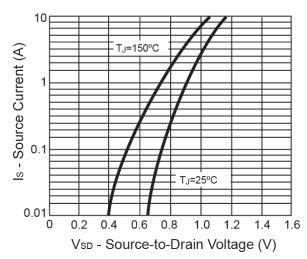
#### **Transfer Characteristics**



## **Gate Charge**



## **Source-Drain Diode Forward Voltage**

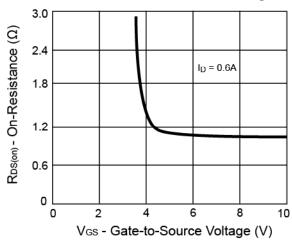




### **CHARACTERISTICS CURVES**

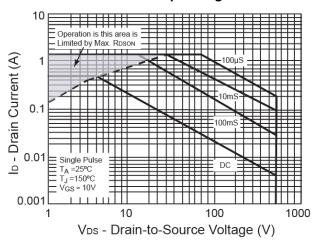
(Tc = 25°C unless otherwise noted)

#### On-Resistance vs. Gate-Source Voltage

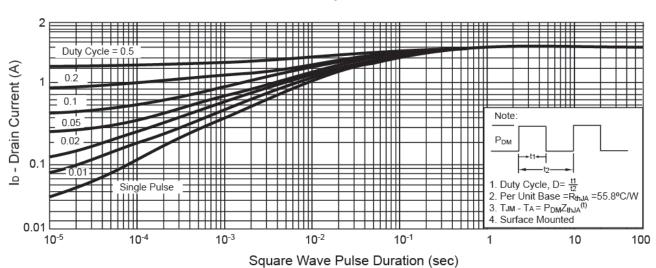


#### **Threshold Voltage** 1.3 Vos(th) - Gate Threshold Voltage 1.2 1.1 $I_D = 250 \mu A$ (Normalized) 1.0 0.9 0.8 0.7 0.6 0.5 -50 -25 25 50 75 100 125 150 Tj - Junction Temperature (°C)

### **Maximum Safe Operating Area**



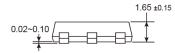
#### Normalized Thermal Transient Impedance, Junction-to-Ambient

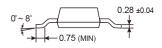




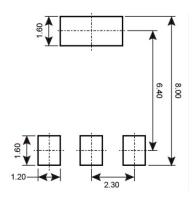
# PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

SOT-223 6.5 ±0.20 3.0 ±0.10 3.0 ±0.10 2.3 (REF) 0.725 ±0.125





## **SUGGESTED PAD LAYOUT**



R =Apr

## **MARKING DIAGRAM**



Y = Year Code

**M** = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar

 $S = May \quad T = Jun \quad U = Jul \quad V = Aug$ 

W = Sep X = Oct Y = Nov Z = Dec

 $\mathbf{L} = \text{Lot Code } (1 \sim 9, A \sim Z)$ 



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